

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-15. (Canceled)
16. (New) An active matrix substrate comprising:
 - a substrate;
 - a source portion formed over the substrate;
 - a drain portion formed over the substrate;
 - a first insulating film formed over the substrate, the first insulating film separating the source portion and the drain portion;
 - a semiconductor layer formed on at least a part of the source portion, at least a part of the drain portion, and at least a part of the first insulating film;
 - a gate insulating layer formed over the semiconductor layer; and
 - a gate electrode formed over the gate insulating layer.
17. (New) The active matrix substrate according to claim 16, further comprising a second insulating film formed around the semiconductor layer, the second insulating film not being formed over the semiconductor layer.
18. (New) The active matrix substrate according to claim 16, further comprising a source electrode contacting the source portion via a first contact hole, the first contact hole being formed at least in the gate insulating layer.
19. (New) The active matrix substrate according to claim 16, further comprising a drain electrode contacting the drain portion via a second contact hole, the second contact hole being formed at least in the gate insulating layer.
20. (New) The active matrix substrate according to claim 16, wherein a thickness of the first insulating film is larger than a thickness of the source portion.

21. (New) The active matrix substrate according to claim 16, wherein the first insulating film is a separation wall surrounding the source portion.
22. (New) The active matrix substrate according to claim 16, wherein the first insulating film includes a silicon oxide.
23. (New) The active matrix substrate according to claim 16, wherein a thickness of a first part of the semiconductor layer on the source portion is different from a thickness of a second part of the semiconductor layer on the first insulating film.
24. (New) The active matrix substrate according to claim 16, wherein a thickness of a first part of the semiconductor layer on the source portion is thinner than a thickness of a second part of the semiconductor layer on the first insulating film.
25. (New) The active matrix substrate according to claim 16, wherein the gate electrode overlaps at least a part of the source portion.
26. (New) An electro-optic device having the active matrix substrate according to claim 16.
27. (New) An electronic instrument having the electro-optic device according to claim 26.